

METHOD FOR PRODUCING SEMICONDUCTOR ENCAPSULATING RESIN
COMPOSITION AND PULVERIZING APPARATUS

ABSTRACT

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A pulverizing apparatus 1 is a gas stream type
pulverizing apparatus. The pulverizing apparatus 1
comprises a pulverizing unit 2 for pulverizing a first
composition, a cooling device 3, a high-pressure air
10 generating device 4 and a collecting unit 5 for receiving
the pulverized first composition. The chamber 6 has a
bottom portion 61, an outlet 62 formed in the bottom
portion for discharging the pulverized first composition
therethrough and a wall portion formed in the bottom
15 portion so as to surround the outlet 62. A plurality of
first nozzles 71 and a second nozzle 72 are provided on a
side portion of the chamber 6 and a tubular supply unit
73 is provided on an upper portion of the second nozzle
72. A pressure of the gas supplied into the chamber is
20 set equal to or more than 0.3 MPa, a temperature of the
gas supplied into the chamber is set equal to or less
than 20°C, and a humidity of the gas supplied into the
chamber is set equal to or less than 40 %RH.

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Figure 2 accompanies the abstract.